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## **NTE4000 & NTE4000T Integrated Circuit CMOS, Dual 3-Input NOR Gate Plus Inverter**

### **Description:**

The NTE4000 (14-Lead DIP) and NTE4000T (SOIC-14) are dual 3-input NOR gate plus inverter devices constructed with MOS P-Channel and N-Channel enhancement mode devices in a single monolithic structure. These complementary MOS logic gates find primary use where low power dissipation and/or high noise immunity is desired.

### **Features:**

- Diode Protection on All Inputs
- Supply Voltage Range: 3Vdc to 18Vdc
- Logic Swing Independent of Fanout

### **Absolute Maximum Ratings:** (Voltages referenced to V<sub>SS</sub>, Note 1)

DC Supply Voltage, V <sub>DD</sub> .....	-0.5 to +18.0V
Input Voltage (DC or Transient), V <sub>in</sub> .....	-0.5 to V <sub>DD</sub> to +0.5V
Output Voltage (DC or Transient), V <sub>out</sub> .....	-0.5 to V <sub>DD</sub> to +0.5V
Input Current (DC or Transient, Per Pin), I <sub>in</sub> .....	±10mA
Output Current (DC or Transient, Per Pin), I <sub>out</sub> .....	±10mA
Power Dissipation (Per Package), P <sub>D</sub> .....	500mW
Temperature Derating (from +65° to +125°C) .....	-7.0mW/°C
Storage Temperature, T <sub>stg</sub> .....	-65° to +150°C
Lead Temperature (During Soldering, 8sec max), T <sub>L</sub> .....	+260°C

Note 1. Maximum Ratings are those values beyond which damage to the device may occur.

**Electrical Characteristics:** (Voltages referenced to V<sub>SS</sub>, Note 2)

Parameter	Symbol	V <sub>DD</sub> Vdc	−55°C		+25°C			+125°C		Unit	
			Min	Max	Min	Typ	Max	Min	Max		
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0	V <sub>OL</sub>	5.0	—	0.05	—	0	0.05	—	0.05	Vdc	
		10	—	0.05	—	0	0.05	—	0.05	Vdc	
		15	—	0.05	—	0	0.05	—	0.05	Vdc	
	V <sub>OH</sub>	5.0	4.95	—	4.95	5.0	—	4.95	—	Vdc	
		10	9.95	—	9.95	10	—	9.95	—	Vdc	
		15	14.95	—	14.95	15	—	14.95	—	Vdc	
Input Voltage (V <sub>O</sub> = 4.5Vdc) (V <sub>O</sub> = 9.0Vdc) (V <sub>O</sub> = 13.5Vdc)	V <sub>IL</sub>	5.0	—	1.0	—	2.25	1.0	—	1.0	Vdc	
		10	—	2.0	—	4.50	2.0	—	2.0	Vdc	
		15	—	2.5	—	6.75	2.5	—	2.5	Vdc	
	V <sub>IH</sub>	5.0	4.0	—	4.0	2.75	—	4.0	—	Vdc	
		10	8.0	—	8.0	5.50	—	8.0	—	Vdc	
		15	12.5	—	12.5	8.25	—	12.5	—	Vdc	
Output Drive Current (V <sub>OH</sub> = 2.5Vdc) (V <sub>OH</sub> = 4.6Vdc) (V <sub>OH</sub> = 9.5Vdc) (V <sub>OH</sub> = 13.5Vdc)	Source	I <sub>OH</sub>	5.0	−1.2	—	−1.0	−1.7	—	−0.7	—	mAdc
		5.0	−0.25	—	−0.2	−0.36	—	−0.14	—	mAdc	
		10	−0.62	—	−0.5	−0.9	—	−0.35	—	mAdc	
		15	−1.8	—	−1.5	−1.5	—	−1.1	—	mAdc	
	Sink	I <sub>OL</sub>	5.0	0.64	—	0.51	0.88	—	0.36	—	mAdc
		10	1.6	—	1.3	2.25	—	0.9	—	mAdc	
		15	4.2	—	3.4	8.8	—	2.4	—	mAdc	
		I <sub>in</sub>	15	—	±0.1	—	±0.00001	±0.1	—	±0.1	μAdc
Input Capacitance (V <sub>IN</sub> = 0)	C <sub>in</sub>	—	—	—	—	5.0	7.5	—	—	pF	
Quiescent Current (Per Package)	I <sub>DD</sub>	5.0	—	0.25	—	0.0005	0.25	—	7.5	μAdc	
		10	—	0.5	—	0.0010	0.5	—	15	μAdc	
		15	—	1.0	—	0.0015	1.0	—	30	μAdc	
Total Supply Current (Dynamic plus Quiescent, Per Gate, C <sub>L</sub> = 50pF, Note 3, Note 4)	I <sub>T</sub>	5.0	I <sub>T</sub> = (0.3μA/kHz) f + I <sub>DD</sub> /N						—	μAdc	
		10	I <sub>T</sub> = (0.6μA/kHz) f + I <sub>DD</sub> /N						—	μAdc	
		15	I <sub>T</sub> = (0.8μA/kHz) f + I <sub>DD</sub> /N						—	μAdc	

Note 2. Data labeled "Typ" is not to be used for design purposes but is intended as an indication of the device's potential performance.

Note 3. The formulas given are for the typical characteristics only at +25°C.

Note 4. To calculate total supply current at loads other than 50pF:

$$I_T(C_L) = I_T(50\text{pF}) + (C_L - 50) V_{fk}$$

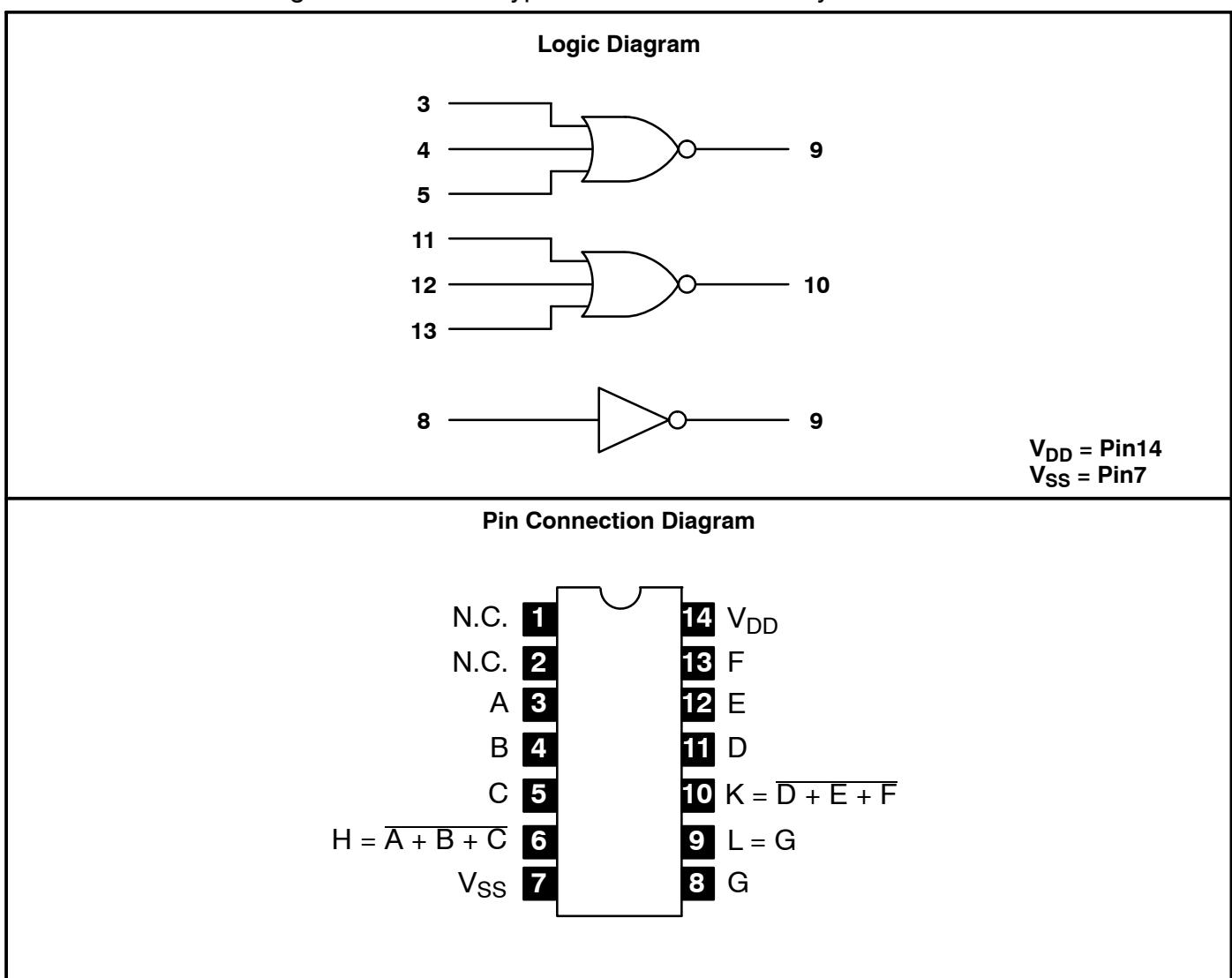
where: I<sub>T</sub> is in μA (per package), C<sub>L</sub> in pF, V = (V<sub>DD</sub> − V<sub>SS</sub>) in volts, f in kHz is input frequency, and k = 0.001 × the number of exercised gates per package.

**Switching Characteristics:** ( $C_L = 50\text{pF}$ ,  $T_A = +25^\circ\text{C}$ , Note 2)

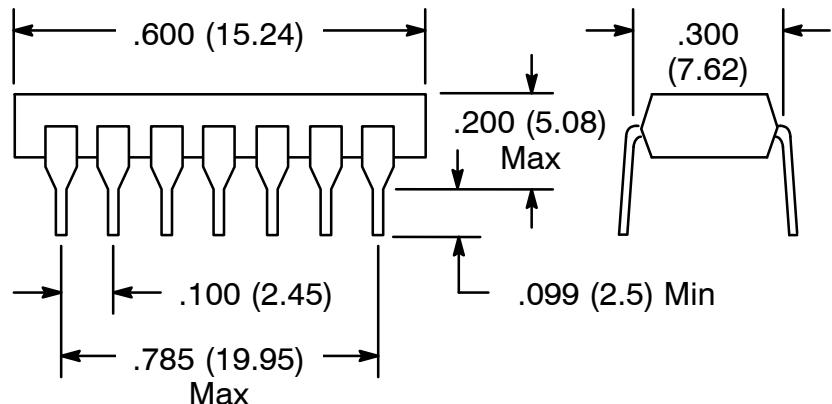
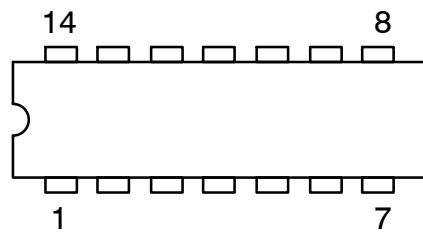
Parameter	Symbol	$V_{DD}$ $V_{dc}$	Min	Typ	Max	Unit
Output Rise Time $t_{TLH} = (3.0\text{ns/pf}) C_L + 30\text{ns}$ $t_{TLH} = (1.5\text{ns/pf}) C_L + 15\text{ns}$ $t_{TLH} = (1.1\text{ns/pf}) C_L + 10\text{ns}$	$t_{TLH}$	5.0	-	180	360	ns
		10	-	90	180	ns
		15	-	65	130	ns
Output Fall Time $t_{THL} = (3.0\text{ns/pf}) C_L + 30\text{ns}$ $t_{THL} = (1.5\text{ns/pf}) C_L + 15\text{ns}$ $t_{THL} = (1.1\text{ns/pf}) C_L + 10\text{ns}$	$t_{THL}$	5.0	-	100	200	ns
		10	-	50	100	ns
		15	-	40	80	ns
Propagation Delay Time $t_{PLH}, t_{PHL} = (1.7\text{ns/pf}) C_L + 30\text{ns}$ $t_{PLH}, t_{PHL} = (0.66\text{ns/pf}) C_L + 22\text{ns}$ $t_{PLH}, t_{PHL} = (0.50\text{ns/pf}) C_L + 15\text{ns}$	$t_{PLH}, t_{PHL}$	5.0	-	115	230	ns
		10	-	55	110	ns
		15	-	40	80	ns

Note 2. Data labeled "Typ" is not to be used for design purposes but is intended as an indication of the device's potential performance.

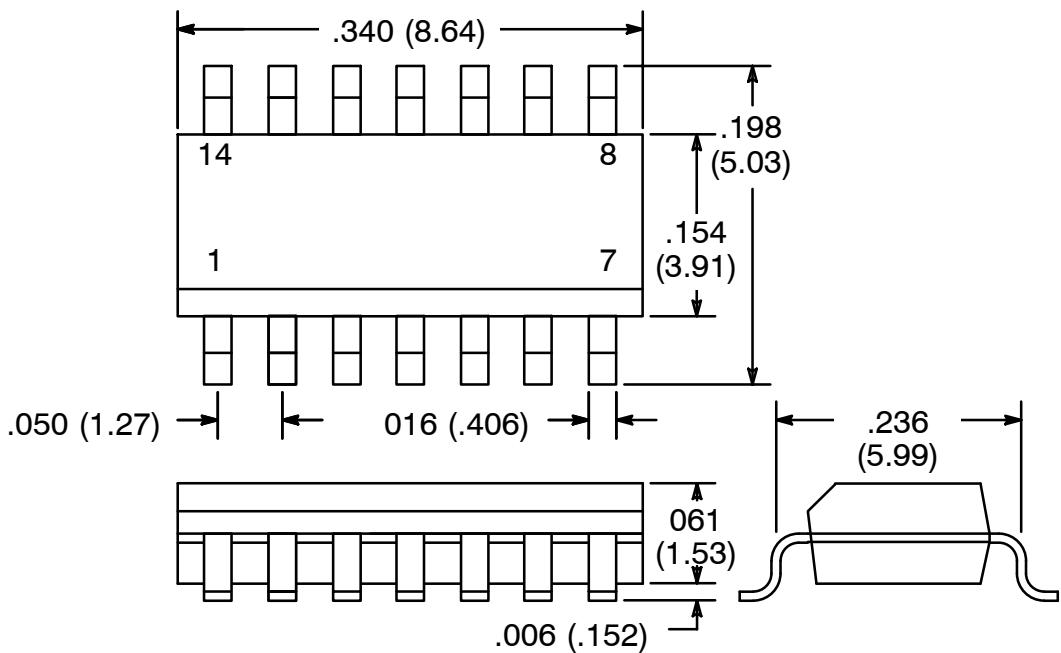
Note 3. The formulas given are for the typical characteristics only at  $+25^\circ\text{C}$ .



### NTE4000



### NTE4000T



NOTE: Pin1 on Beveled Edge